MGBR60L100C DIODE

# DUAL MOS GATED BARRIER RECTIFIER

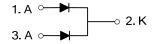
#### DESCRIPTION

The UTC **MGBR60L100C** is a dual mos gated barrier rectifiers, it uses UTC's advanced technology to provide customers with low forward voltage drop and high switching speed, etc.

#### ■ FEATURES

- \* Low forward voltage drop
- \* High switching speed

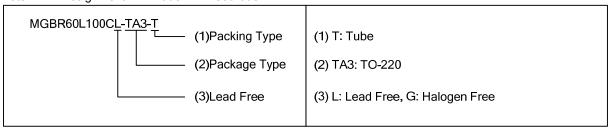
## ■ SYMBOL



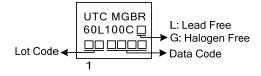
# ORDERING INFORMATION

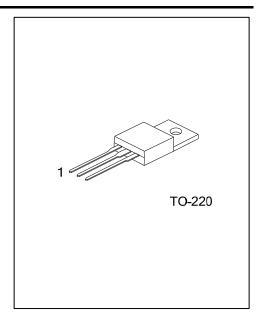
Ordering Number		Dackago	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
MGBR60L100CL-TA3-T	MGBR60L100CG-TA3-T	TO-220	Α	K	Α	Tube	

Note: Pin Assignment: A: Anode K: Cathode



## MARKING





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# ■ ABSOLUTE MAXIMUM RATINGS (PER LEG) (T<sub>A</sub>=25°C unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by 20%.

PARAMETER	SYMBOL	RATINGS	UNIT	
DC Blocking Voltage	$V_{RM}$	100	V	
Working Peak Reverse Voltage	$V_{RWM}$	100	V	
Peak Repetitive Reverse Voltage		$V_{RRM}$	100	V
Average Restified Output Current Per Device	Per Leg		30	Α
Average Rectified Output Current Per Device	Total	Io	60	Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load		I <sub>FSM</sub>	280	Α
Operating Junction Temperature		$T_J$	-65~+150	°C
Storage Temperature		$T_{STG}$	-65~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

#### ■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	$\theta_{JA}$	62.5	°C/W
Junction to Case	$\theta_{ m JC}$	2	°C/W

# ■ ELECTRICAL CHARACTERISTICS (PER LEG) (T<sub>A</sub> =25°C unless otherwise specified.)

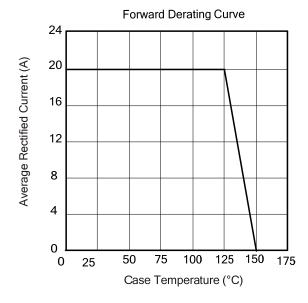
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage (Note 1)	$V_{(BR)R}$	I <sub>R</sub> =0.50mA	100			V
Farmerd Voltage Dage	I VEM	I <sub>F</sub> =30A, T <sub>J</sub> =25°C			0.79	V
Forward Voltage Drop		I <sub>F</sub> =30A, T <sub>J</sub> =125°C			0.74	V
Lastrana Comment (Nata 4)	DM	V <sub>R</sub> =100V, T <sub>J</sub> =25°C			200	μA
Leakage Current (Note 1)		V <sub>R</sub> =100V, T <sub>J</sub> =125°C			20	mA

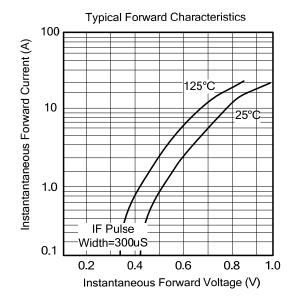
Notes: 1. Short duration pulse test used to minimize self-heating effect.

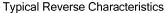
<sup>2.</sup> Thermal resistance junction to case mounted on heatsink.

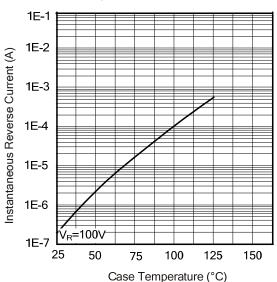
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## ■ TYPICAL CHARACTERISTICS









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